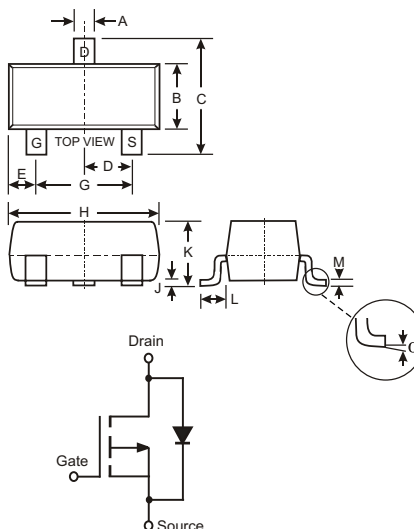


P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR
Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Also Available in Lead Free Version

Mechanical Data

- Case: SOT-23, Molded Plastic
- Case material - UL Flammability Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish). Please see Ordering Information, Note 4, on Page 2
- Terminal Connections: See Diagram
- Marking (See Page 2): K84
- Ordering & Date Code Information: See Page 2
- Weight: 0.008 grams (approx.)



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Maximum Ratings N-CHANNEL - 2N7002 Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	BSS84	Units
Drain-Source Voltage	V_{DS}	-50	V
Drain-Gate Voltage $R_{GS} \leq 20\text{K}\Omega$	V_{DGR}	-50	V
Gate-Source Voltage Continuous	V_{GSS}	± 20	V
Drain Current (Note 1) Continuous	I_D	-130	mA
Total Power Dissipation (Note 1)	P_d	300	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)						
Drain-Source Breakdown Voltage	BV _{DSS}	-50	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-15	μA	V _{DS} = -50V, V _{GS} = 0V, T _J = 25°C
		—	—	-60	μA	V _{DS} = -50V, V _{GS} = 0V, T _J = 125°C
		—	—	-100	nA	V _{DS} = -25V, V _{GS} = 0V, T _J = 25°C
Gate-Body Leakage	I _{GSS}	—	—	±10	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	V _{GS(th)}	-0.8	—	-2.0	V	V _{DS} = V _{GS} , I _D = -1mA
Static Drain-Source On-Resistance	R _{DS (ON)}	—	—	10	Ω	V _{GS} = -5V, I _D = 0.100A
Forward Transconductance	g _{FS}	0.05	—	—	S	V _{DS} = -25V, I _D = 0.1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	—	45	pF	V _{DS} = -25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	12	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	—	10	—	ns	V _{DD} = -30V, I _D = -0.27A, R _{GEN} = 50Ω, V _{GS} = -10V
Turn-Off Delay Time	t _{D(OFF)}	—	18	—	ns	

Note: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

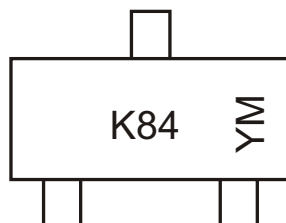
2. Short duration test pulse used to minimize self-heating effect.

Ordering Information (Note 3)

Device	Packaging	Shipping
BSS84-7	SOT-23	3000/Tape & Reel

- Notes:
- For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.
 - For Lead Free version (with Lead Free terminal finish) part number, please add "-F" suffix to part number above.
Example: BSS84-7-F.

Marking Information



K84 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: N = 2002
 M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

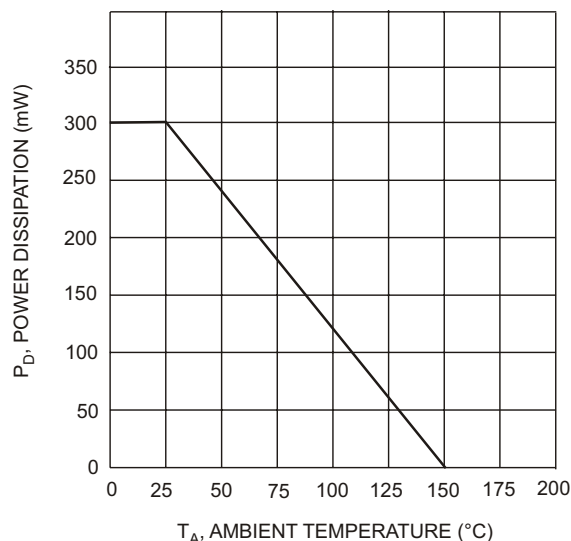


Fig. 1, Max Power Dissipation vs. Ambient Temperature

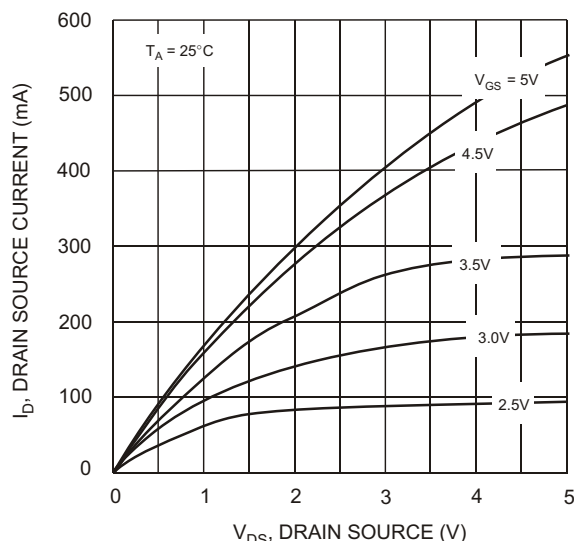


Fig. 2, Drain Source Current vs. Drain Source Voltage

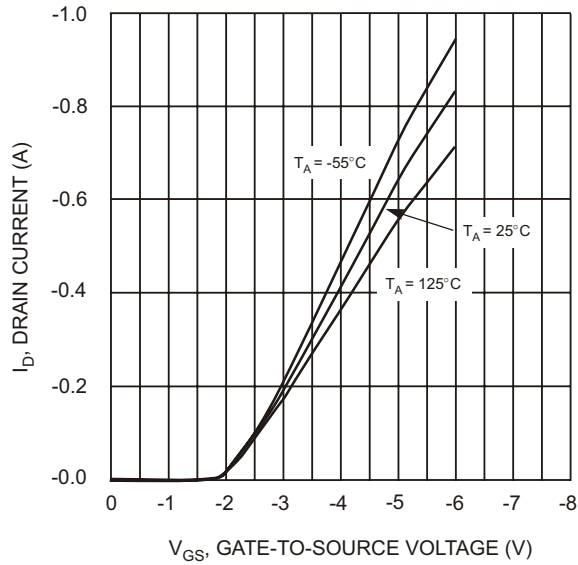


Fig. 3, Drain Current vs. Gate Source Voltage

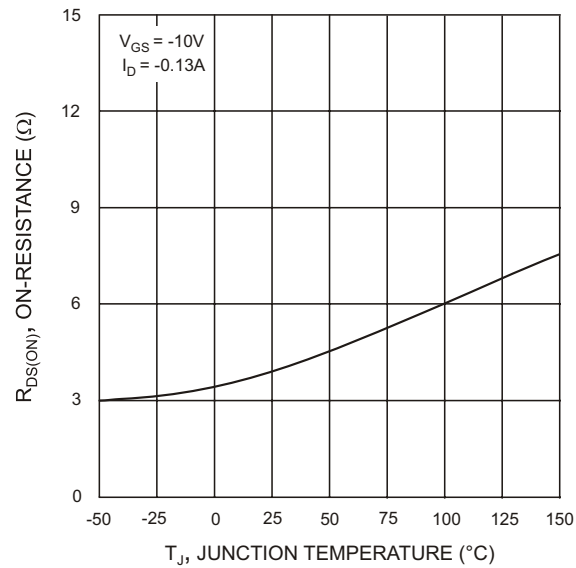


Fig. 5, On-Resistance vs. Junction Temperature

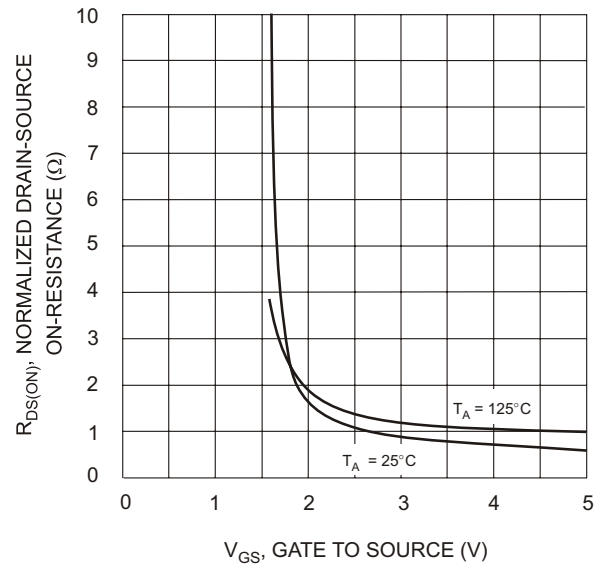


Fig. 4, On Resistance vs. Gate Source Voltage

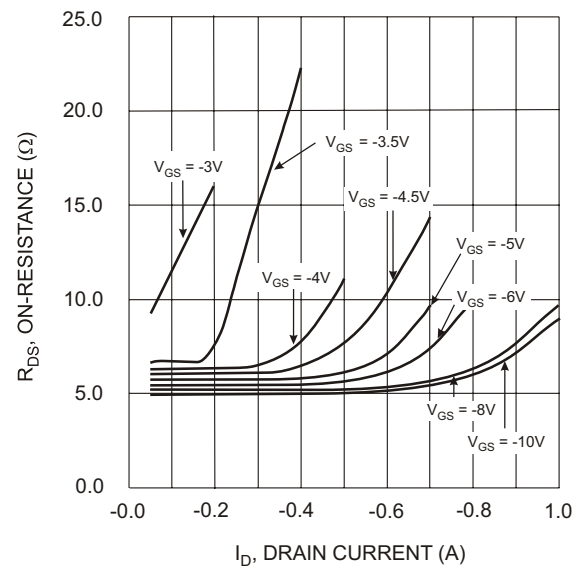


Fig. 6, On-Resistance vs. Drain Current